

FIG.1a (PRIOR ART)

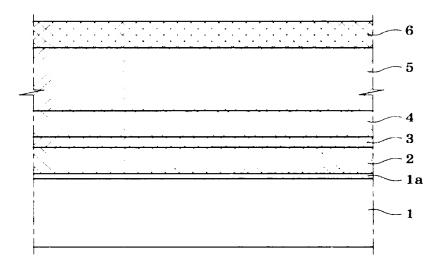
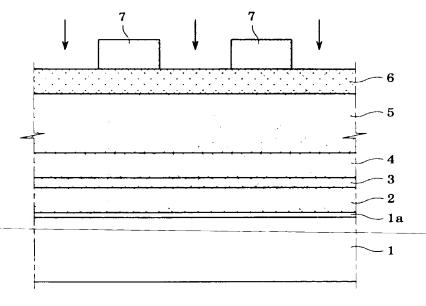


FIG.1b (PRIOR ART)



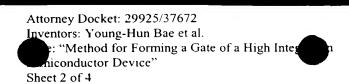


FIG.1c (PRIOR ART)

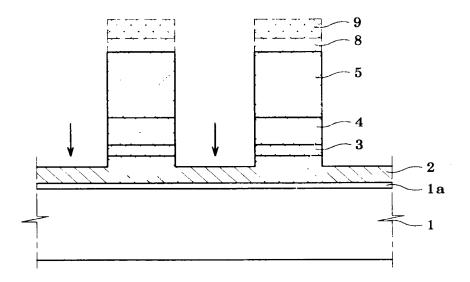
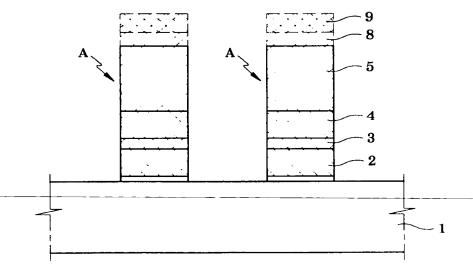


FIG.1d (PRIOR ART)



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FIG.2a

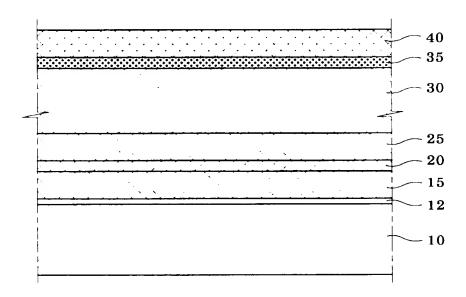
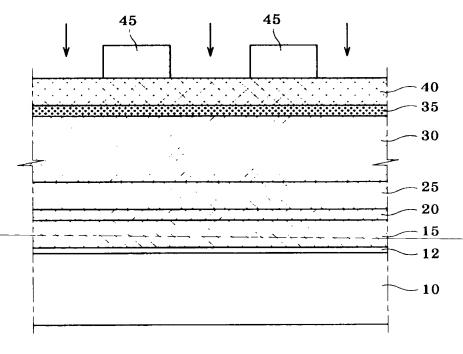


FIG.2b



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FIG.2c

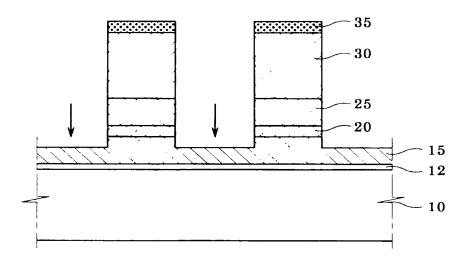


FIG.2d

